



## Compact and Low-Power Time to Digital Converters for High Granularity Silicon Detectors

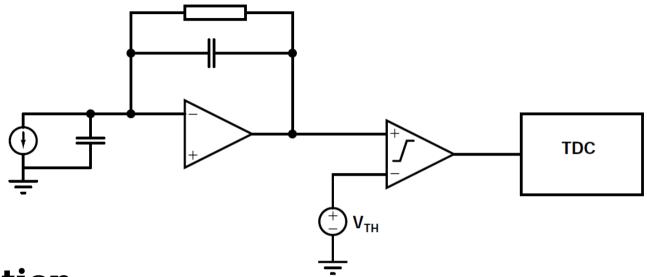
Angelo Rivetti INFN-Sezione di Torino, Italy











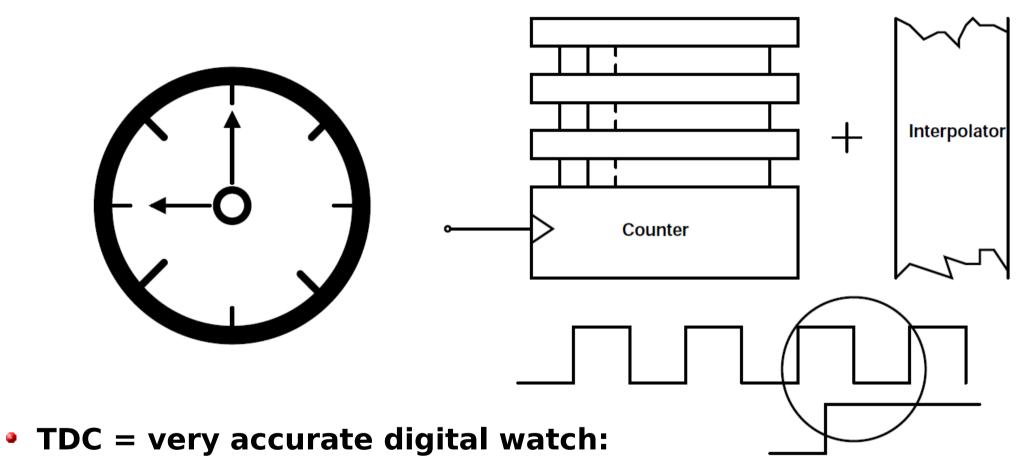
#### Introduction

- Overview of recent trends
- TDC for distributed systems:
  - Ring oscillators
  - Time to amplitude
- Conclusion and outlook



#### **TDC** basics





- Sub 100 ps resolution;
- Multi-channel (> 100) ;
- Compact, low power and high rates.

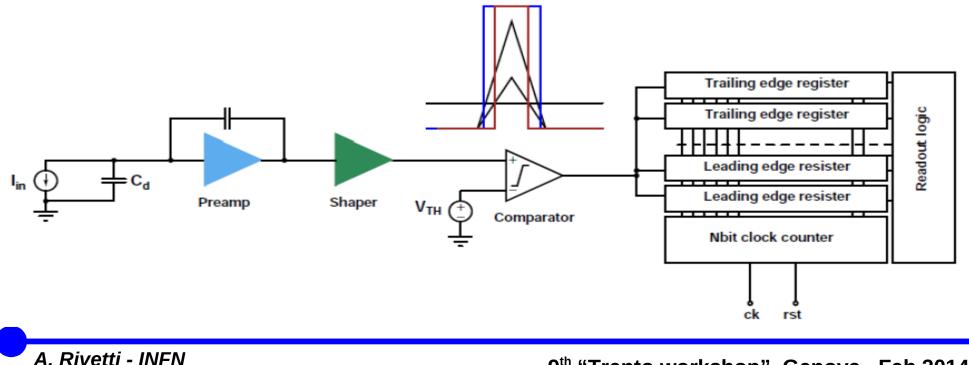
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- Indispensable in high granularity timing systems:
  - Time resolved photon counting (analog and digital silicon PM).
  - 4-D Tracking in HEP
  - **Time-domain ADC.**

 TDC=only digital gates or (in a few cases) analog circuits with low dynamic range: suitable for deep submicron technologies.





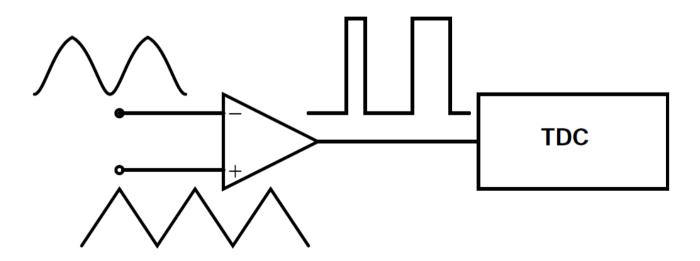
#### Time-based ADC



IEEE JOURNAL OF SOLID-STATE CIRCUITS, VOL. 46, NO. 9, SEPTEMBER 2011

# A 0.8 ps DNL Time-to-Digital Converter With 250 MHz Event Rate in 65 nm CMOS for Time-Mode-Based $\Sigma\Delta$ Modulator

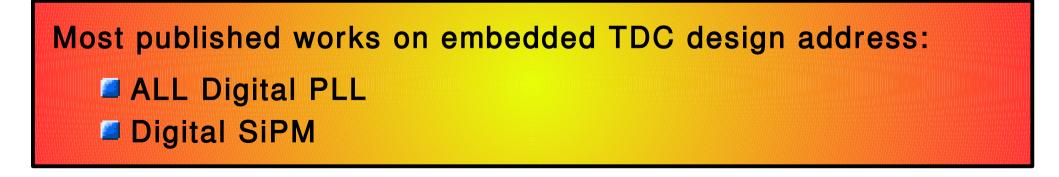
Mohamed M. Elsayed, Student Member, IEEE, Vijay Dhanasekaran, Member, IEEE, Manisha Gambhir, Member, IEEE, Jose Silva-Martinez, Fellow, IEEE, and Edgar Sánchez-Sinencio, Life Fellow, IEEE







- TDCs were traditionally stand-alone components implemented on dedicated chips.
- Increasing interest in embedded solutions, where the converter is part of more complex ASICs.
- Area and power consumption are key parameters for embedded designs.
- ULSI technologies (130 nm and below) not indispensable for very good time resolution...
- ...but needed for compact cell size and low power.

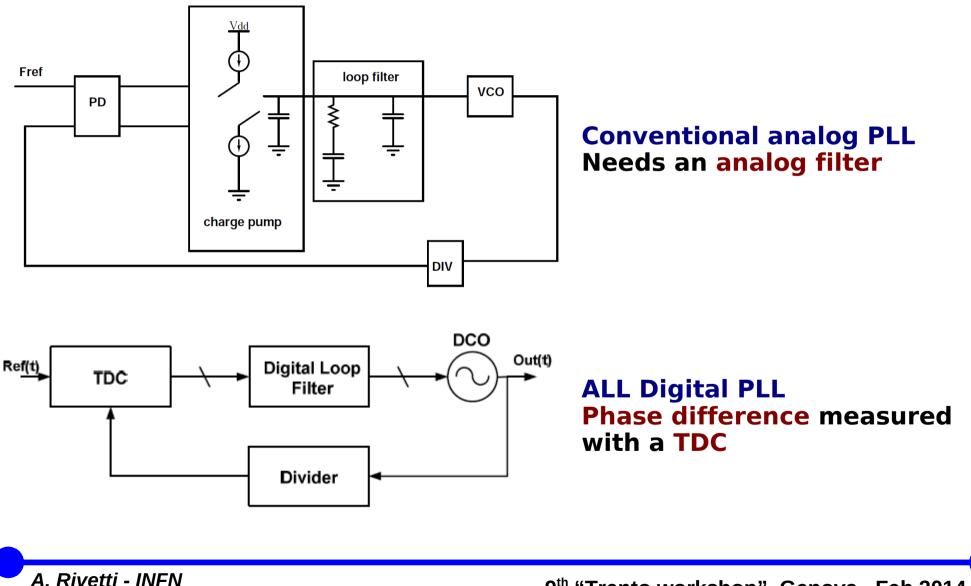




TDC in ADPLL (1)



Due to ADPLL, TDC became more general purpose components, with an significant increase on the number of published papers in the recent years.





#### TDC in ADPLL (2)



| Ref | Technology | Architecture   | Resolut<br>ion (ps) | Sampling rate (MS/s) | Range (ns) | Power<br>(mW) | Area<br>(mm²) |
|-----|------------|----------------|---------------------|----------------------|------------|---------------|---------------|
| 1   | 130 nm     | GRO            | 1                   | 50                   | 12         | 2.2-21        | 0.04          |
| 2   | 130 nm     | Vernier-ring   | 8                   | 15                   | 32         | 7.5           | 0.26          |
| 3   | 90 nm      | Passive inter. | 4.7                 | 180                  | 0.6        | 3.6           | 0.02          |
| 4   | 90 nm      | Delay line     | 20                  | 26                   | 0.64       | 6.9           | 0.01          |
| 5   | 65 nm      | 2D delay line  | 4.8                 | 50                   | < 0.6      | 1.7           | 0.02          |
| 6   | 90         | Time Amp.      | 1.25                | 10                   | 0.64       | 3             | 0.6           |
| 7   | 90         | Vernier+GRO    | 3.2                 | 25-100               | 40         | 3.6-4.5       | 0.027         |

**TDC** in ADPLL targets extremely good resolution;

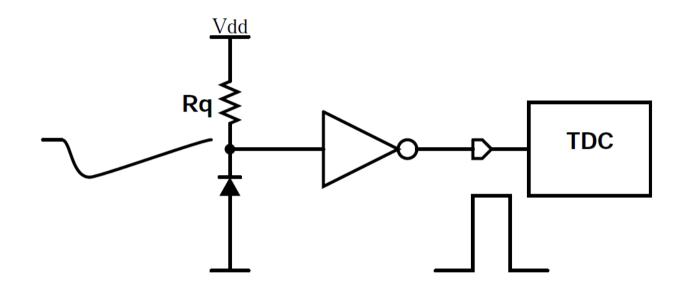
- Dynamic range less of a concern;
- Many different architectures;

Timing resolution of future detectors will not be limited by the TDC.



#### TDCs in digital SiPM (1)





Geiger mode sensor + front-end electronics in single chip;

Typical pixel size: 50 um x 50 um to 300 um x 300 um;
Sensor design not trivial: HV CMOS or imaging

process used.





# TDCs in digital SiPM (2)



| Ref | Technology    | Architecture | LSB<br>(ps) | Range (ns) | Power<br>(mW) | Area              | Dead<br>time (ns) |
|-----|---------------|--------------|-------------|------------|---------------|-------------------|-------------------|
| 1   | 130 nm<br>CIS | Delay lines  | 62.5        | 64         |               |                   |                   |
| 2   | 350 nm HV     | Delay lines  | 80          | 3.5        |               |                   |                   |
| 3   | 350 nm        | Delay lines  | 10          | 160        | 15            | 0.3 mm2           | 150               |
| 4   | 130 nm        | GRO          | 55          | 55         | 0.64          | < 50 um<br>x50 um |                   |
| 5   | 130n          | GRO          | 64.56       | 261.59     | 1 mW          |                   |                   |

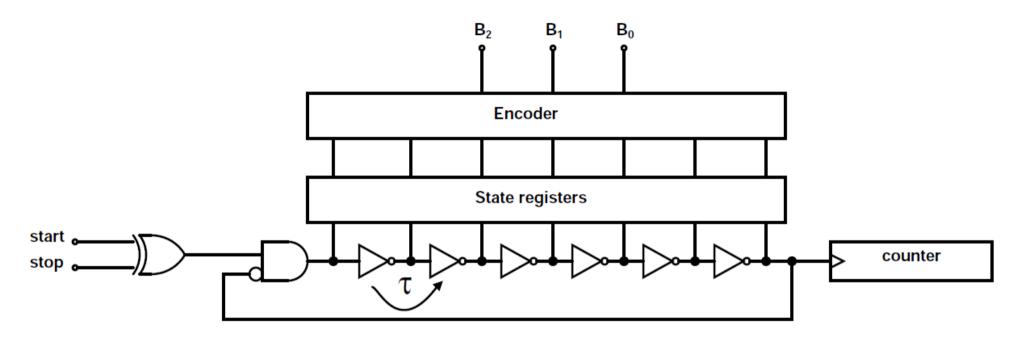
#### Massive parallelism

Low power

Good but not extreme time resolution

## Ring oscillators

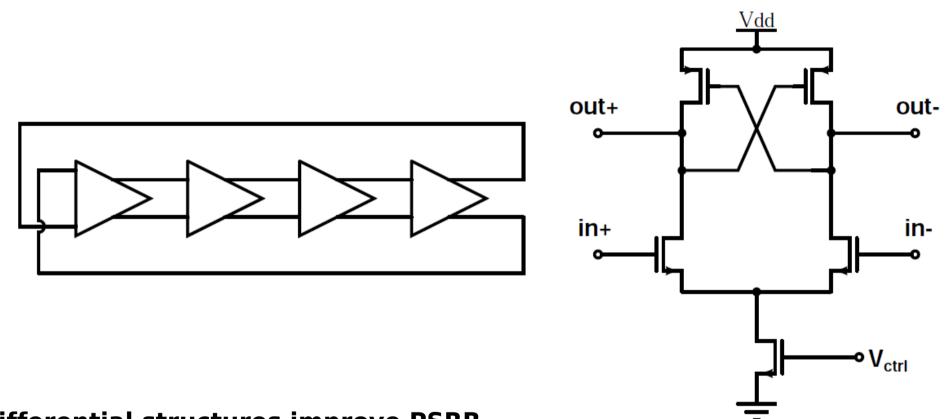




- Feed-back loop encompassing an odd number of inversions
- Binning=τ
- Latency=1/(N<sub>t</sub>)
- Oscillator active only when measuring.
- Compact and low power. Adequate as local TDC in pixellated systems.
- Sensitive to: Process, Voltage Supply, Temperature (PVT), matching...





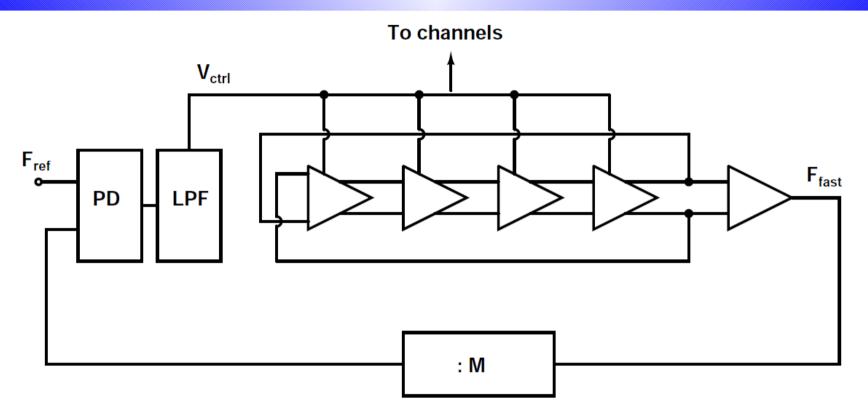


- Differential structures improve PSRR
- Both phases can be used: 8 states from 4 differential cells
- PVT not yet adequate for high performance TDC.



# **PVT** stabilization through **PLL**





- Ideally, each oscillator should be controlled by a PLL loop: cumbersome for distributed implementation (LPF area).
- Replica oscillator in PLL and distribution of the control low frequency si gnal.
- Mismatch between oscillators an issue.





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This article has been accepted for inclusion in a future issue of this journal. Content is final as presented, with the exception of pagination.

IEEE TRANSACTIONS ON NUCLEAR SCIENCE

#### GOSSIPO-4: Evaluation of a Novel PLL-Based TDC-Technique for the Readout of GridPix-Detectors

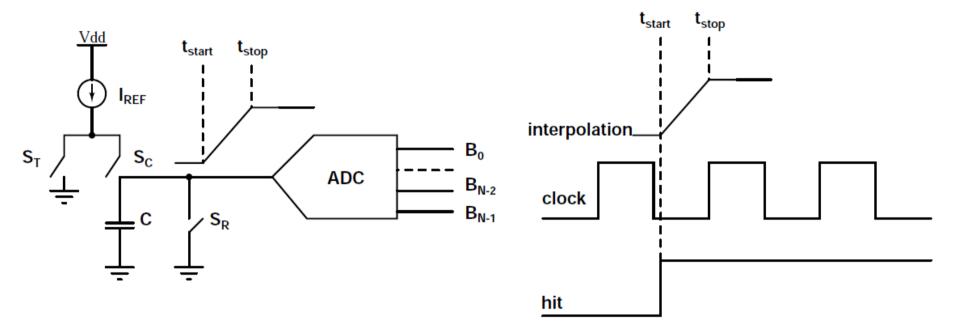
C. Brezina, Y. Fu, F. Zappon, M. van Beuzekom, M. Campbell, K. Desch, H. van der Graaf, V. Gromov, R. Kluit, X. Llopart, T. Poikela, and V. Zivkovic

• 640 MHz ring oscillator.

- 1.56 ns binning.
- 40 MHZ x 16 clock multiplication





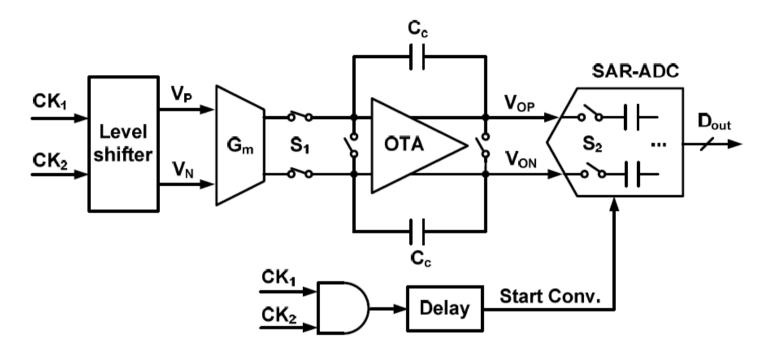


- Charge a capacitor for the time to be measured and digitize the voltage.
- Requires ADC
- $\bullet$  Today SAR ADC: 10 bit, 50 MS/s, 1 mW, 300  $\mu m$  x 300  $\mu m$  in 0.13  $\mu m$  CMOS
- Interpolate 6.25 ns with 10 bits: 6 ps.
- Area for a 7 bit ADC (48 ps binning) 80  $\mu$ m x 80  $\mu$ m.
- Conversion time: O (50 ns)
- Estimated power at 1 MHz rate: < 0.5 mW</p>



## **Recent** design and performance





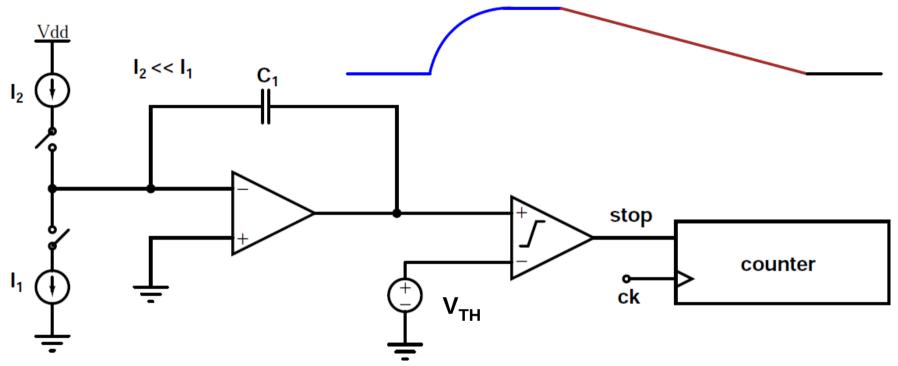
Zule Xu, Masaya Miyahara, and Akira Matsuzawa A 1ps-Resolution Integrator-Based Time-to-Digital Converter Using a SAR-ADC in 90nm CMOS IEEE 2013 NeW System and Circuit Conference (NEWCAS)

- Time bin: 1ps
- Range: 9 bits
- Power: 20 mW



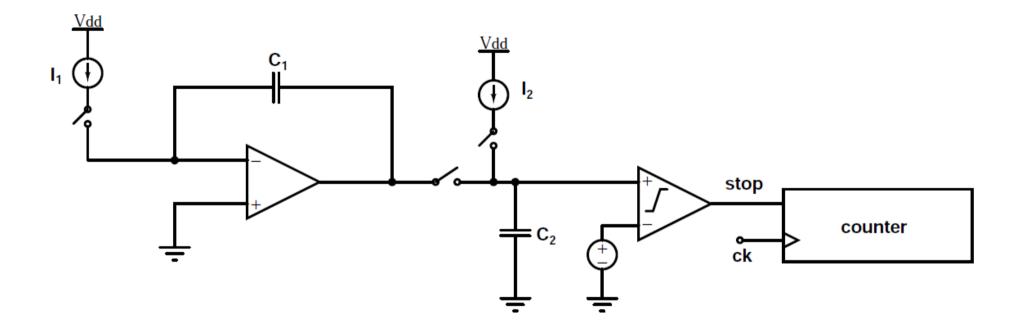
#### The simplest: TAC + Wilkinson





- Current flowing in opposite directions: NMOS and PMOS current sourcematching issue.
- $I_1$  larger than  $I_2$ : output impedance of  $I_1$  smaller: virtual ground helps, although not indispensable.
- Amplifier does not need to keep a linear rising edge: bandwidth not a major issue.
- Clock: 12.5 ns: binning 100 ps I<sub>1</sub>/I<sub>2</sub> 128





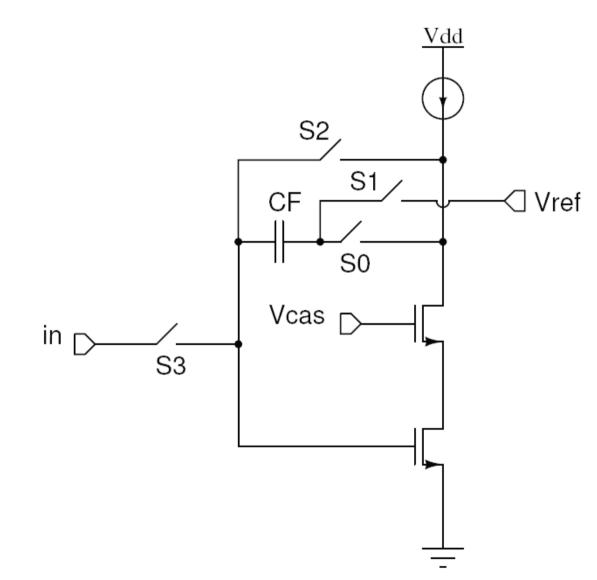
- Charge is transferred on C<sub>2</sub>
- $C_2 = 4C_1$
- Ck=2 TDCck
- I<sub>1</sub>/I<sub>2</sub>=16

- Compact design
- Only capacitor and current ratio counts
- Easy to calibrate
- PVT stable
- Time interleaving for moderate rates (up to 1 MHz/channel)



#### TAC detail





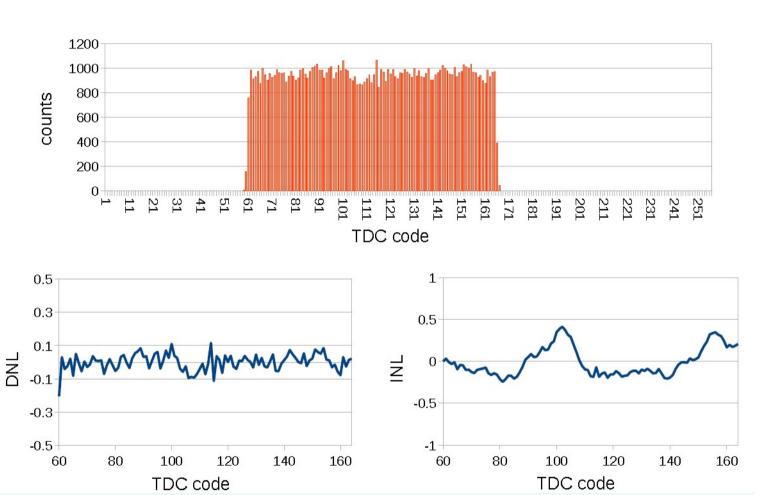
1. Reset/Arming: S0, S3 open, S2, S1 closed

2. Idle S0 closed, S1, S2, S3 open

3. Charging S3, S0 closed, S1, S2 open.



#### DNL – INL testing





bration + bias circuitry

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Analog

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bias circuitry

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Front

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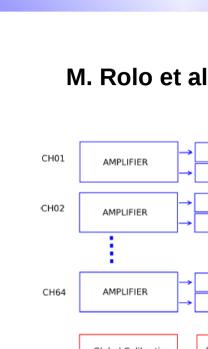
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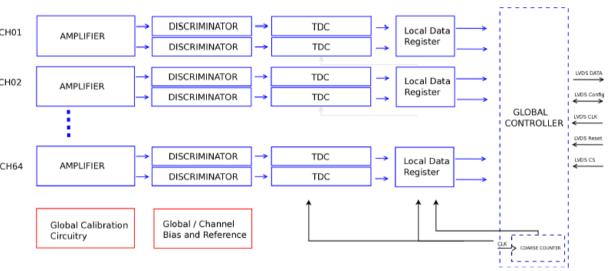
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#### **Example of chip using TAC**



#### M. Rolo et al. "TOFPET ASIC for PET applications

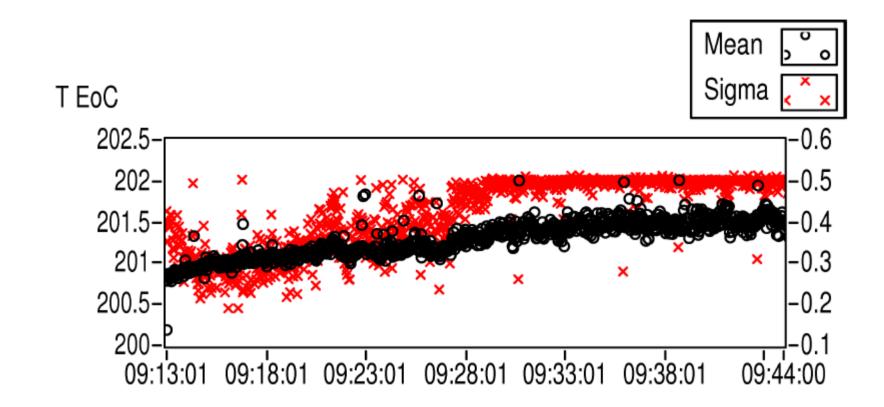


#### Readout for analog SiPM

2 TDC per channel with four time-interleaved TAC Scalable binning down to 25 ps. Rate > 100 kHz per channel





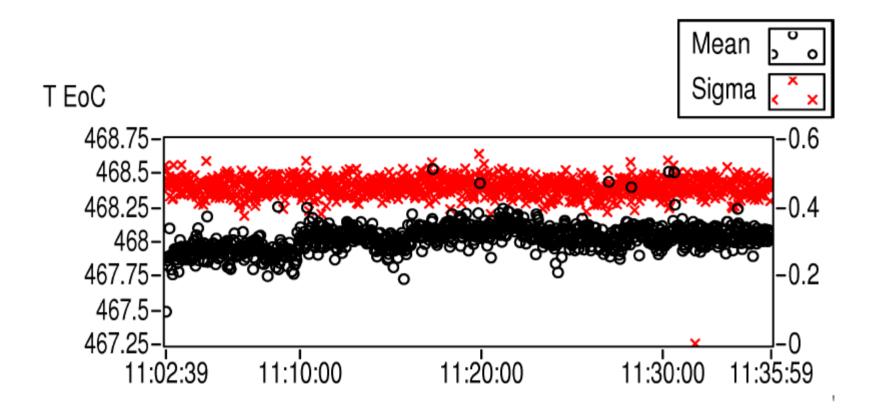


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#### Long term stability



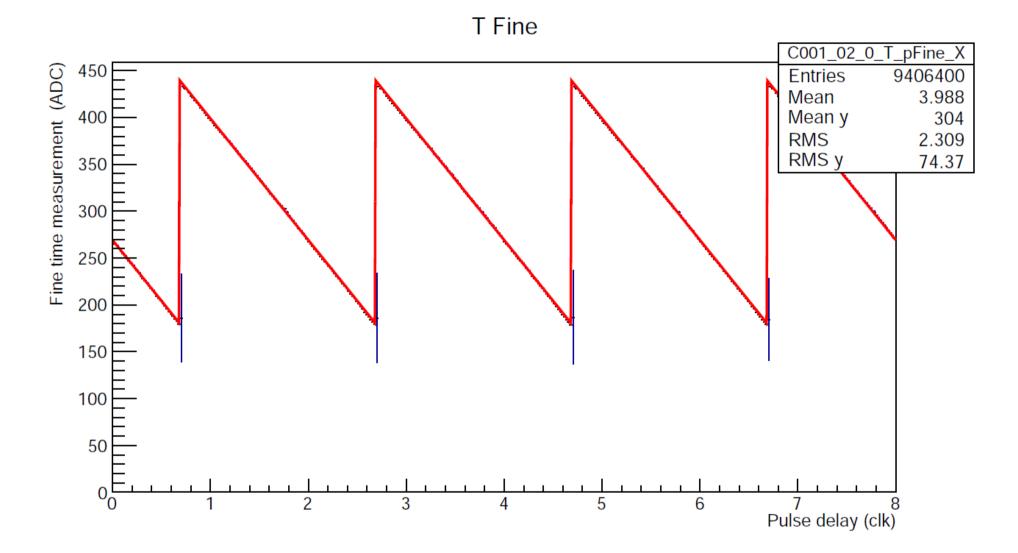


- In SC circuits important to check long term stability
- Potential problems from charge build-up due to incomplete reset.
- TDC running at 80 kHz average rate



#### Fine time pattern...

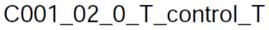


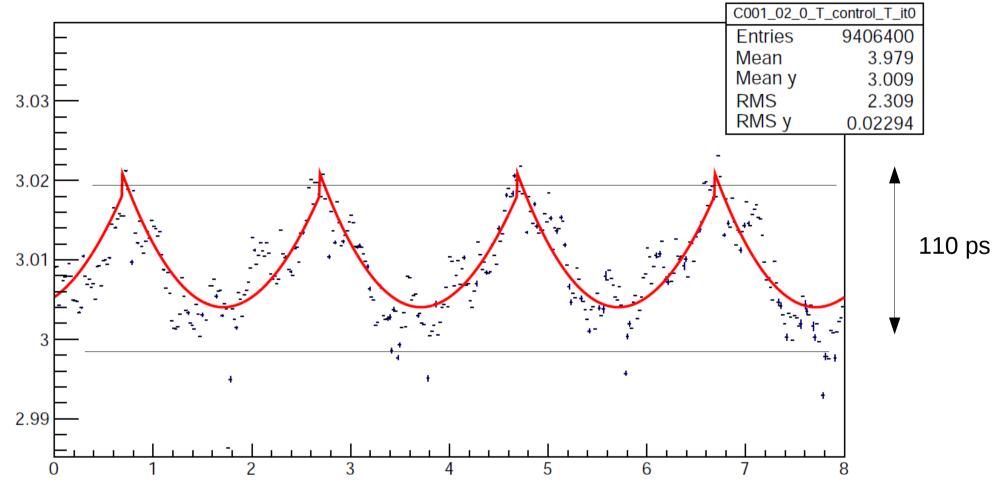


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#### **Residual non-linearity**



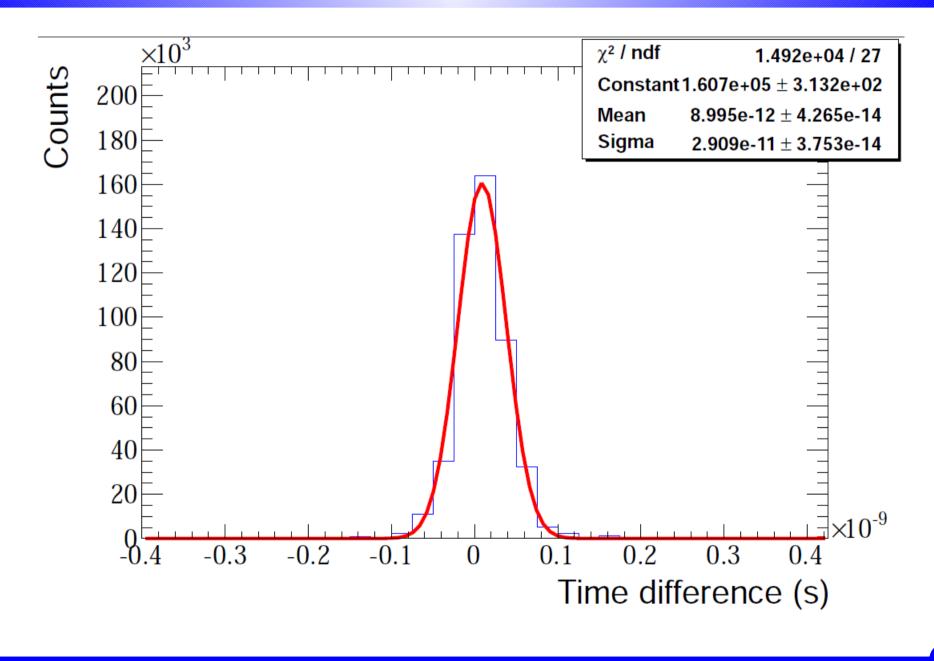




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#### Limits on timing: jitter



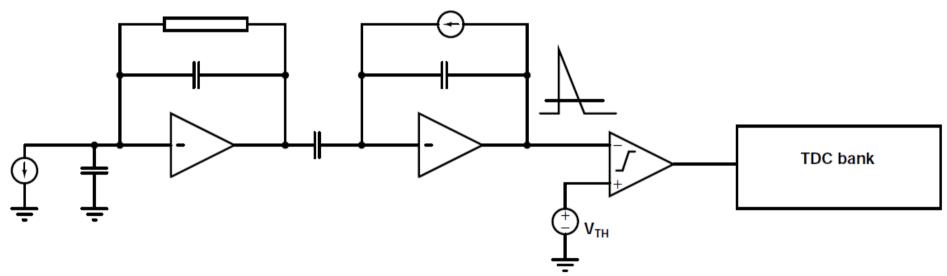
9<sup>th</sup> "Trento workshop" Genova, Feb 2014

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- On going project for the PANDA MVD.
- Triggerless detectors with 10E7  $p\overline{p}$  interactions per second.
- Rate O(40 kHz)/strip
- Time resolution O (ns)....



- FAST ToT + TDC
- ToT stage can saturate still providing a linear charge measurement
- Sampling the charge using only timing circuitry.
- Slower clock + interpolation provides smaller power





- A lot of progress recently made in TDC design.
- TDC can be implemented on a per-channel basis in front-en ASIC for radiation detectors.
- Time base readout=accurate timing plus charge information with basically only digital circuitry.
- Electronics is ready for high granularity and high resolution timing system.
- Hitting sub-100 ps time resolution is mostly on the shoulder of sensor designers....



#### References



#### • SPAD TDC

**1. R. M. Field et al,** A 100-fps, Time-Correlated Single-Photon- Counting-Based Fluorescence-Lifetime Imager in 130-nm **to be published in IEEE J. Solid-State Circ., April 2014.** 

**2. I. Nissinen et al.,** *A time-gated 4x128 SPAD array with a 512 channel flash 80 ps-TDC for pulsed Raman spectroscopy*, **2013 IEEE ECCTD Conf. Records.** 

**3. B. Markovic et al.,** A High-Linearity, 17 ps Precision Time-to-Digital Converter Based on a Single-Stage Vernier Delay Loop Fine Interpolation, IEEE Trans. Circ. Syst. I, vol. 60, March 2013.

**4. C. Veerappan et al.,** A 160x128 single-photon image sensor with on-pixel 55ps 10b time-to-digital converter, **ISSCC, Feb. 2011.**